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## N-Channel 150 V (D-S) MOSFET

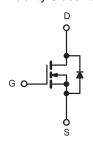
PRODUCT SUMMARY						
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (mΩ) (Typ.)	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)			
150	3.6 at V <sub>GS</sub> = 10 V	176	94 nC			

#### **FEATURES**

- DT-Trench Power MOSFET
- 100 % Rg and UIS tested
- DC/DC in Telecoms and Inductrial
- · Synchronous Rectification in SMPS

#### **APPLICATIONS**

- Green Molding Compound
- Moisture Sensitivity
- UL Flammability Classification Rating 94V-0



N-Channel MOSFET



Top View

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-Source Voltage	V <sub>DS</sub>	150	V			
Gate-Source Voltage	V <sub>GS</sub>	± 20	V			
Continuous Dunin Courset (T., 175 °C)'s	T <sub>C</sub> = 25 °C		176	А		
Continuous Drain Current (T <sub>J</sub> = 175 °C) <sup>a</sup>	T <sub>C</sub> = 100 °C	I <sub>D</sub>	125			
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	705				
Single Avalanche Energy	E <sub>AS</sub>	1795	mJ			
Movimum Boursy Dissinctions	T <sub>C</sub> = 25 °C	В	333	W		
Maximum Power Dissipation <sup>c</sup>	T <sub>C</sub> = 100 °C	P <sub>D</sub>	167	] vv		
Operating Junction and Storage Temperature Ra	T <sub>J</sub> , T <sub>stg</sub>	- 55 to +175	°C			

THERMAL RESISTANCE RATINGS						
PARAMETER	SYMBOL	LIMIT	UNIT			
Junction-to-Ambient (PCB Mount) <sup>d</sup>	R <sub>thJA</sub>	31	°C/W			
Junction-to-Case (Drain)	R <sub>thJC</sub>	0.45	C/VV			

#### Notes

- a. Calculated continuous current based on maximum allowablejunction temperature.
- b. Repetitive rating; pulse width limited by max. junction temperature.
- c. Pd is based on max. junction temperature, using junction-case thermal resistance.
- d. The value of R<sub>0JA</sub> is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper,in a still air environment with Ta=25 °C.



<b>SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	150	-	-	V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2.5	-	4.5	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	=	-	± 100	nA	
Zero Gate Voltage Drain Current	1	V <sub>DS</sub> = 150V, V <sub>GS</sub> = 0 V	=	-	1		
Zero date voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 150 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C	-	-	100	μA Ο	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	176	-	-	Α	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A	=	3.6	4.6	mΩ	
Forward Transconductance a	9 <sub>fs</sub>	V <sub>DS</sub> = 5 V, I <sub>D</sub> = 20 A	-	58	-	S	
Dynamic <sup>b</sup>				•			
Input Capacitance	C <sub>iss</sub>		-	5980	-	pF	
Output Capacitance	C <sub>oss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 75 V, f = 1 MHz	-	777	-		
Reverse Transfer Capacitance	C <sub>rss</sub>		-	21	-		
Total Gate Charge <sup>c</sup>	Qg		-	94	-	nC	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>DS</sub> = 75 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A	-	22	-		
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$		-	25	-		
Gate Resistance	$R_g$	f = 1 MHz	-	2.4	-	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>		-	20	=		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 75 \text{ V}, I_D = 20 \text{ A}, R_g = 3\Omega$	-	41	-	ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	V <sub>GS</sub> = 10 V	-	58	-		
Fall Time <sup>c</sup>	t <sub>f</sub>		-	44	-		
Drain-Source Body Diode Ratings and	Characterist	tics <sup>b</sup> (T <sub>C</sub> = 25 °C)					
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	-	-	176	Α	
Pulsed Current	I <sub>SM</sub>		-	-	705	Α	
Forward Voltage <sup>a</sup>	$V_{SD}$	I <sub>F</sub> = 1 A, V <sub>GS</sub> = 0 V	-	-	1.2	V	
Reverse Recovery Time	t <sub>rr</sub>	1 = 20 A di/d+ 100 A/	-	103	-	ns	
Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> = 20 A, di/dt = 100 A/μs	=	430	-	nC	

#### Notes

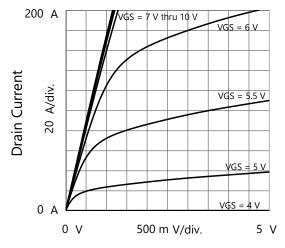
- a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

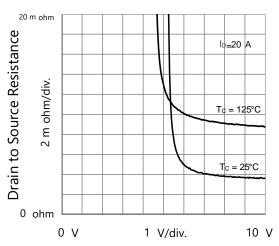




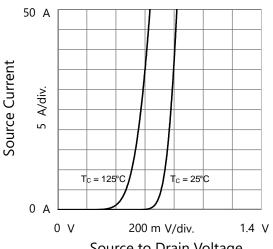
#### TYPICAL CHARACTERISTICS (25 C, unless otherwise noted)



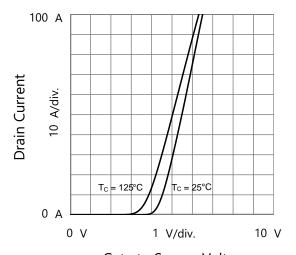
Drain to Source Voltage Output Characteristics



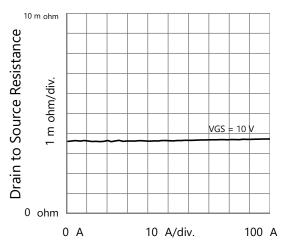
Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltage



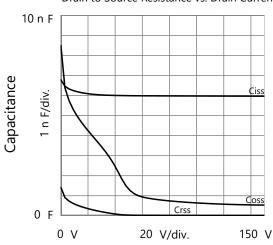
Source to Drain Voltage Body Diode Forward Characteristics



Gate to Source Voltage Transfer Characteristics



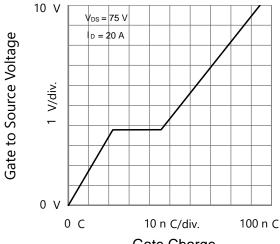
Drain Current
Drain to Source Resistance vs. Drain Current



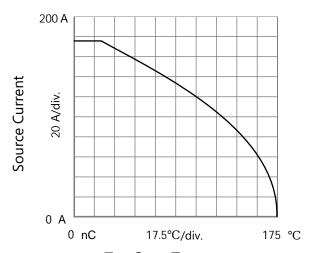
Drain to Source Voltage Capacitances



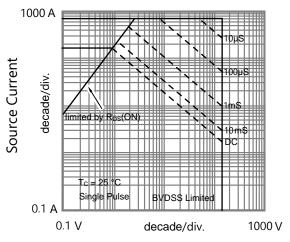
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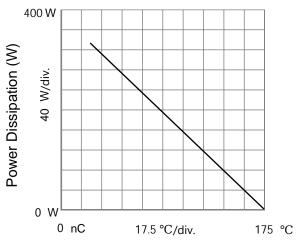
Gate Charge
Gate to Source Voltage vs. GateCharge



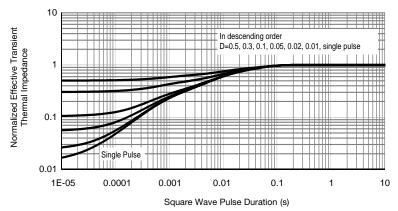
T<sub>C</sub> - Case Temperature



Source to Drain Voltage Safe Operating Area, Junction-to-Ambient



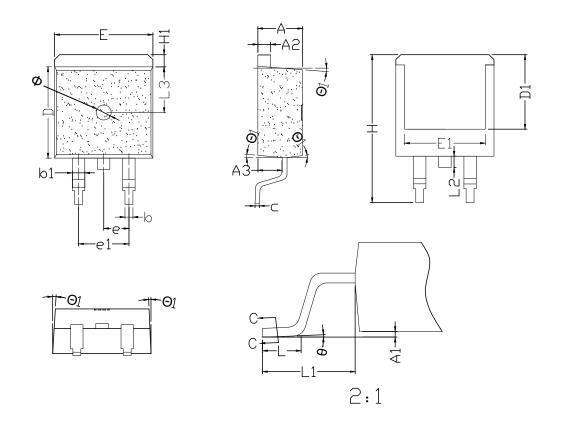
T<sub>C</sub> - Case Temperature



Normalized Thermal Transient Impedance, Junction-to-Case



# **TO-263 PACKAGE OUTLINE**



**COMMON DIMENSIONS** (UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	TYP	MAX	SYMBOL	MIN	TYP	MAX
Α	4.10	4.50	4.80	е	2.35	2.54	2.75
A1	0.00	0.10	0.30	e1	5.08REF		
A2	1.10	1.30	1.50	Н	14.50	15.15	16.00
A3	2.15	2.50	3.10	H1	1.00	1.28	1.75
b	0.60	0.80	1.05	L	1.80	2.23	2.90
b1	1.05	1.33	1.50	L1	4.30	4.75	5.50
С	0.33	0.50	0.66	L2	1.00	1.30	1.85
D	8.40	9.20	9.60	L3	0.90	4.65	9.00
D1	7.50REF		ф	0°	2°	5°	
E	9.60	10.02	10.80	φ1	2°	-	7°
E1	7.60	9.88	10.30	Φ	1.5BSC		

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